

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau

(43) International Publication Date
05 December 2024 (05.12.2024)



(10) International Publication Number
WO 2024/249216 A1

(51) International Patent Classification:

H10B 43/27 (2023.01) H01L 29/792 (2006.01)
H10B 43/35 (2023.01) H01L 29/66 (2006.01)

(21) International Application Number:

PCT/US2024/030589

(22) International Filing Date:

22 May 2024 (22.05.2024)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

63/470,647 02 June 2023 (02.06.2023) US

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(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

(54) Title: FORMATION OF MEMORY DEVICE CHANNEL HOLES USING DOPED FILM LAYER

(57) Abstract: Disclosed are approaches for fabricating memory device channel holes using a doped film layer. One approach may include providing a substrate and forming a vertical stack over the substrate, wherein the vertical stack includes a plurality of alternating material layers. The method may further include forming a channel hole through the vertical stack, forming an oxide-nitride-oxide layer along a sidewall of the channel hole, forming a silicon layer over the oxide-nitride-oxide layer, forming an etch stop layer over the silicon layer, forming a fluorine-doped silicon layer over the etch stop layer, and annealing the vertical stack.

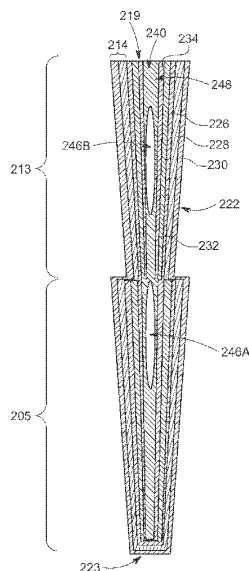


FIG. 3C

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Published:

— with international search report (Art. 21(3))